100V NPN LOW SATURATION MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

SUMMARY

 $BV_{CEO} = 100V : R_{SAT} = 36m\Omega; I_C = 6A$

DESCRIPTION

Packaged in the SOT223 outline this new low saturation 100V NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

FEATURES

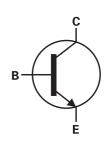
- 6 amps continuous current
- Up to 10 amps peak current
- Very low saturation voltages

APPLICATIONS

- Motor driving
- Line switching
- High side switches
- Subscriber line interface cards (SLIC)



SOT223



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXTN2011GTA	7″	12mm	1,000 units
ZXTN2011GTC	13″	embossed	4,000 units

DEVICE MARKING

ZXTN 2011 | |

С

Ε

С

В

PINOUT



TOP VIEW

ISSUE 2 - MAY 2006

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	BV _{CBO}	200	V
Collector-emitter voltage	BV _{CEO}	100	V
Emitter-base voltage	BV _{EBO}	7	V
Continuous collector current ^(a)	Ι _C	6	А
Peak pulse current	I _{CM}	10	А
Power dissipation at $T_A = 25^{\circ}C^{(a)}$	PD	3.0	W
Linear derating factor		24	mW/°C
Power dissipation at T _A =25°C ^(b)	PD	1.6	W
Linear derating factor		12.8	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

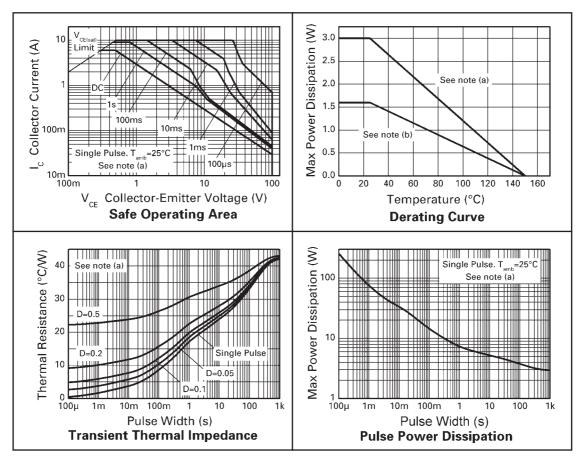
THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient ^(a)	$R_{\Theta JA}$	42	°C/W

NOTES

(a) For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions. (b) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.





CHARACTERISTICS

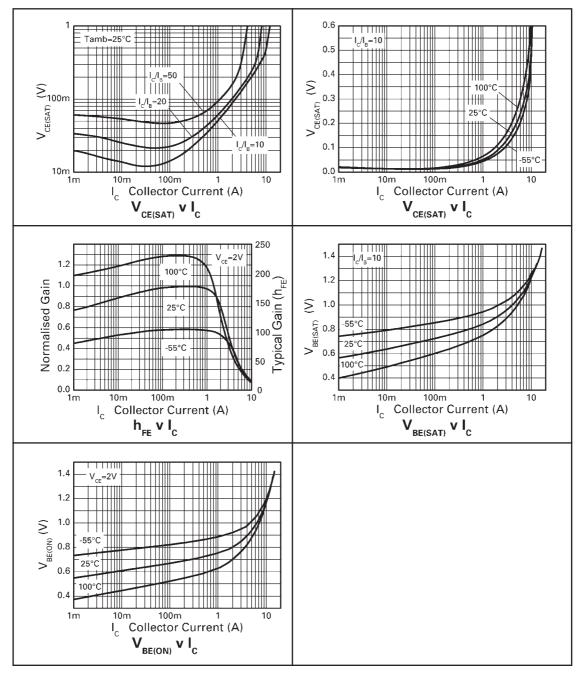


PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	BV _{CBO}	200	235		V	I _C =100μA
Collector-emitter breakdown voltage	BV _{CER}	200	235		V	I _C =1μA, RB≤1kΩ
Collector-emitter breakdown voltage	BV _{CEO}	100	115		V	I _C =10mA*
Emitter-base breakdown voltage	BV _{EBO}	7	8.1		V	I _E =100μA
Collector cut-off current	I _{CBO}			50	nA	V _{CB} =150V
				0.5	μA	V _{CB} =150V,T _{amb} =100°C
Collector cut-off current	I _{CER}			100	nA	V _{CB} =150V
	$R\leq1k\Omega$			0.5	μA	V _{CB} =150V,T _{amb} =100°C
Emitter cut-off current	I _{EBO}			10	nA	V _{EB} =6V
Collector-emitter saturation voltage	V _{CE(SAT)}		21	35	mV	I _C =0.1A, I _B =5mA*
			50	65	mV	I _C =1A, I _B =100mA*
			95	125	mV	I _C =2A, I _B =100mA*
			180	220	mV	I _C =5A, I _B =500mA*
Base-emitter saturation voltage	V _{BE(SAT)}		1020	1120	mV	I _C =5A, I _B =500mA*
Base-emitter turn-on voltage	V _{BE(ON)}		920	1000	mV	I _C =5A, V _{CE} =2V*
Static forward current transfer ratio	H _{FE}	100	230			I _C =10mA, V _{CE} =2V*
		100	200	300		I _C =2A, V _{CE} =2V*
		30	60			I _C =5A, V _{CE} =2V*
		10	20			I _C =10A, V _{CE} =2V*
Transition frequency	f _T		130		MHz	I _C =100mA, V _{CE} =10V
						f=50MHz
Output capacitance	C _{OBO}		26		pF	V _{CB} =10V, f=1MHz*
Switching times	t _{ON}		41		ns	I _C =1A, V _{CC} =10V,
	t _{OFF}		1010			I _{B1} =I _{B2} =100mA

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

* Measured under pulsed conditions. Pulse width \leq 300 $\mu s;$ duty cycle $\leq \!\! 2\%.$

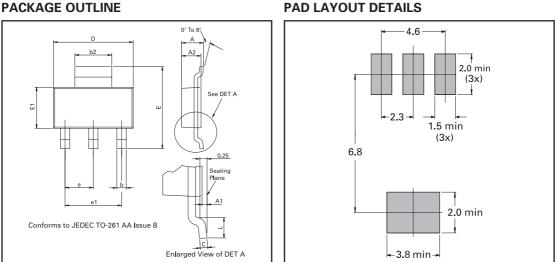




TYPICAL CHARACTERISTICS



PACKAGE OUTLINE



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
	Min	Max	Min	Мах		Min	Мах	Min	Мах
А	-	1.80	-	0.071	е	2.30	BSC	0.090	5 BSC
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
С	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

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